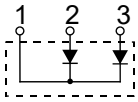
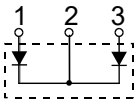
SDKF2X350-02B

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

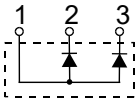


SDKF2X350-02B1
Side Common

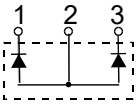


SDKF2X350-02B2
Center Common

	VRSM V	VRRM V
SDKF2x350-02B1	200	200
SDKF2x350-02B2	200	200



SDAF2X350-02B1
Side Common



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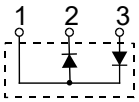
Center Common



SDEF2X350-02B1
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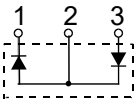
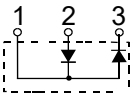
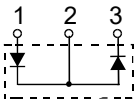


SDEF2X350-02B2
Center Common

	VRSM V	VRRM V
SDAF2x350-02B1	200	200
SDAF2x350-02B2	200	200



SDFF2X350-02B1
Side Common



SDFF2X350-02B2
Center Common

	VRSM V	VRRM V
SDFF2x350-02B1	200	200
SDFF2x350-02B2	200	200

Symbol	Test Conditions		Maximum Ratings	Unit
I_{FRMS} I_{FAVM} I_{FRM}	T_C=75°C T_C=75°C; rectangular, d=0.5 , per chip t_P<10us; rep. rating, pulse width limited by T_{VJM}		550 350 1800	A
I_{FSM}	T_{VJ}=45°C	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	5400 2640	A
	T_{VJ}=150°C	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	2160 2380	
I^2t	T_{VJ}=45°C	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	28800 29300	A^2s
	T_{VJ}=150°C	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	23300 23800	
T_{VJ} T_{stg} T_{Smax}			-40...+150 -40...+125 110	°C
P_{tot}	T_C=25°C		875	W
V_{ISOL}	50/60Hz, RMS t=1min I_{ISOL}≤1mA t=1s		3000 3600	V~
M_d	Mounting torque (M6) Terminal connection torque (M6)		2.25-2.75/20-25 4.50-5.50/40-48	Nm/lb.in.
d_S d_A a	Creeping distance on surface Strike distance through air Maximum allowable acceleration		12.7 9.6 50	mm mm m/s^2
Weight			150	g

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SDKF2X350-02B

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	T_{VJ}=25°C; V_R=V_{RRM} T_{VJ}=25°C; V_R=0.8·V_{RRM} T_{VJ}=125°C; V_R=0.8·V_{RRM}		3 2 80	mA
V_F	I_F=175A; T_{VJ}=125°C T_{VJ}=25°C I_F=350A; T_{VJ}=125°C T_{VJ}=25°C		0.80 0.98 0.92 1.07	V
V_{TO}	For power-loss calculations only		0.53	V
r_T			1.29	mΩ
R_{thJH} R_{thJC}	DC current DC current		0.228 0.143	K/W
t_{rr} I_{RM}	I_F=350A; T_{VJ}=100°C V_R=100V; T_{VJ}=25°C -di/dt=200A/us; T_{VJ}=100°C	150	200 9 15	ns A A

FEATURES

* International standard package
* Copper Baseplate
* Planar passivated chips
* Short recovery time
* Low switching losses
* Soft recovery behaviour
* Isolation voltage 3600 V~
* RoHS compliant

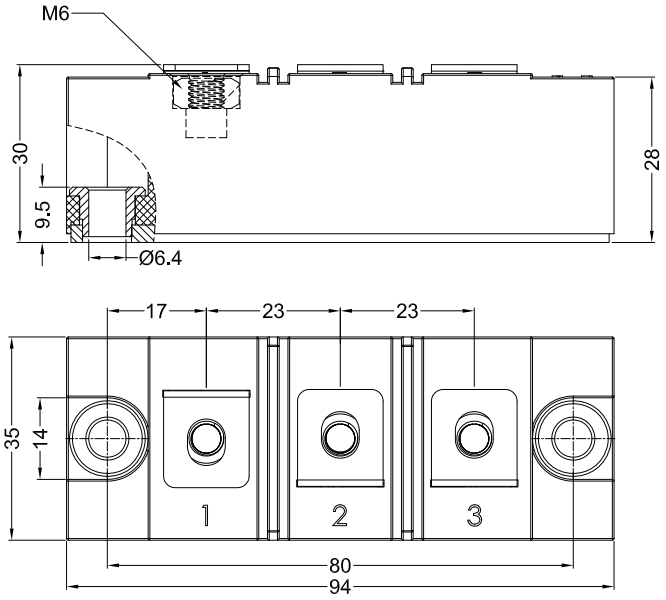
APPLICATIONS

* Antiparallel diode for high frequency switching devices
* Free wheeling diode in converters and motor control circuits
* Inductive heating and melting
* Uninterruptible power supplies (UPS)
* Ultrasonic cleaners and welders

ADVANTAGES

* High reliability circuit operation
* Low voltage peaks for reduced protection circuits
* Low noise switching
* Low losses

Dimensions in mm



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SDKF2X350-02B

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

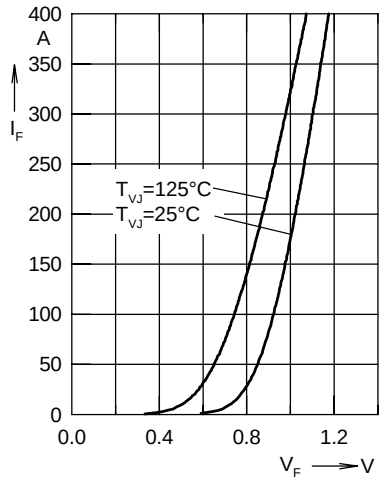

Fig. 1 Forward current I_F versus voltage drop V_F per leg

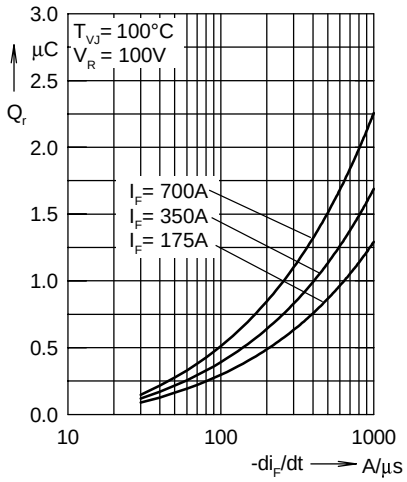

Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

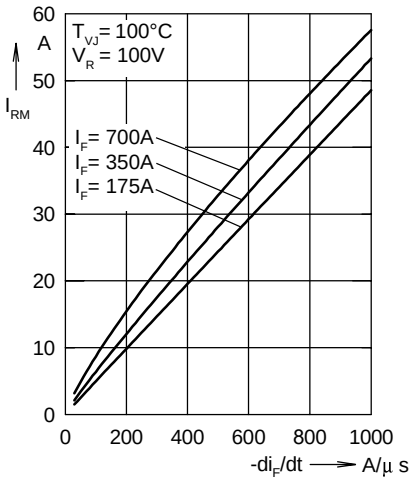

Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

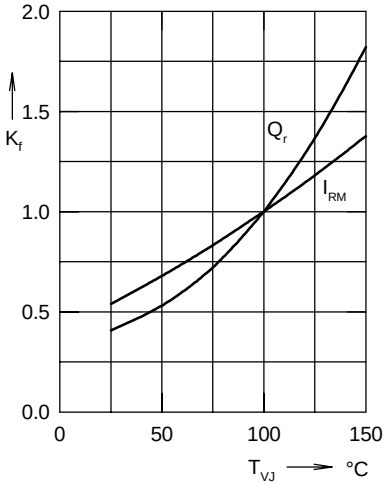

Fig. 4 Dynamic parameters Q_r, I_{RM} versus junction temperature T_{VJ}

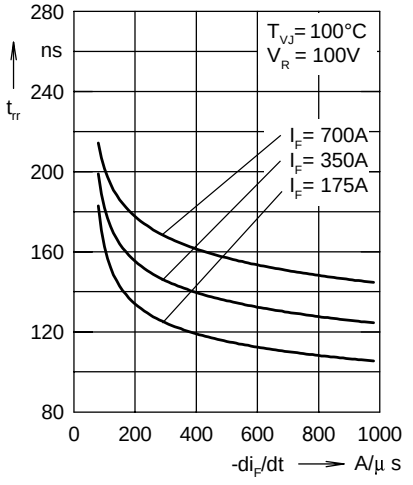

Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

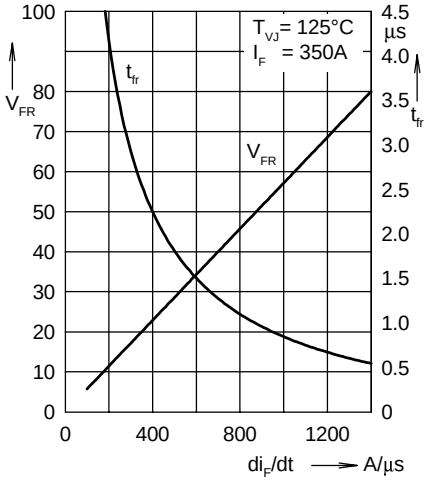

Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

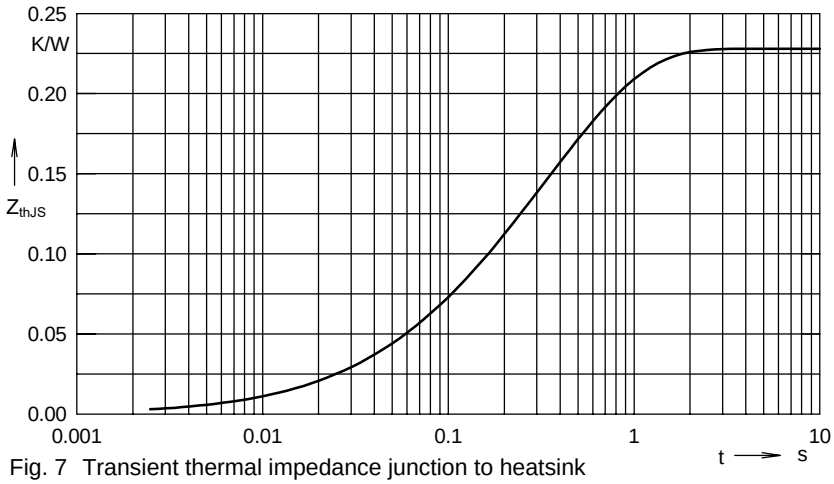

Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJS} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.002	0.08
2	0.008	0.024
3	0.054	0.112
4	0.164	0.464

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